

**Description**

The SX4P05MI uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

**General Features**

$V_{DS} = -55V$   $I_D = -4.2A$

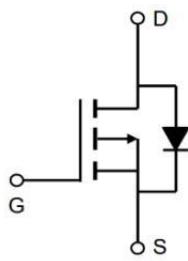
$R_{DS(ON)} < 125m\Omega$  @  $V_{GS} = -10V$

**Application**

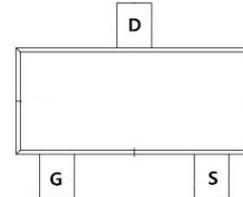
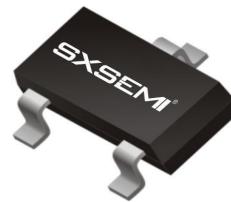
Battery protection

Load switch

Uninterruptible power supply



SOT-23-3L

**Absolute Maximum Ratings ( $T_c = 25^\circ C$  unless otherwise noted)**

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	-55	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-4.2	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-2.4	A
$IDM$	Pulsed Drain Current <sup>2</sup>	-16	A
$P_D @ T_A = 25^\circ C$	Total Power Dissipation <sup>3</sup>	1	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	125	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	80	$^\circ C/W$

**Electrical Characteristics (TC=25 °C unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =-250uA	-55	-58	---	V
△BVDSS/△T <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C , I <sub>D</sub> =-1mA	---	-0.021	---	V/°C
RDS(ON)	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =-10V , I <sub>D</sub> =-1.5A	---	108	125	mΩ
		V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-1A	---	125	155	mΩ
VGS(th)	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> = -250uA	-1.0	1.6	-2.5	V
△V <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	4.08	---	mV/°C
IDSS	Drain-Source Leakage Current	V <sub>DS</sub> =-48V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C	---	---	1	uA
IDSS		V <sub>DS</sub> =-48V , V <sub>GS</sub> =0V , T <sub>J</sub> =55°C	---	---	5	
IGSS	Gate-Source Leakage Current	V <sub>GS</sub> =±20V , V <sub>DS</sub> =0V	---	---	±100	nA
gfs	Forward Transconductance	V <sub>DS</sub> =-5V , I <sub>D</sub> =-1.5A	---	5.9	---	S
Q <sub>g</sub>	Total Gate Charge (-4.5V)	V <sub>DS</sub> =-20V , V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-1.5A	---	4.6	---	nC
Qgs	Gate-Source Charge		---	1.4	---	nC
Qgd	Gate-Drain Charge		---	1.62	---	nC
Td(on)	Turn-On Delay Time	V <sub>DS</sub> =-15V , V <sub>GS</sub> =-10V , R <sub>G</sub> =3.3Ω, I <sub>D</sub> =-1A	---	17.4	---	ns
T <sub>r</sub>	Rise Time		---	5.4	---	ns
Td(off)	Turn-Off Delay Time		---	37.2	---	ns
T <sub>f</sub>	Fall Time		---	2.4	---	ns
Ciss	Input Capacitance	V <sub>DS</sub> =-15V , V <sub>GS</sub> =0V , f=1MHz	---	531	---	pF
Coss	Output Capacitance		---	59	---	pF
Crss	Reverse Transfer Capacitance		---	38	---	pF
IS	Continuous Source Current <sup>1,4</sup>	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current	---	---	-1.7	A
ISM	Pulsed Source Current <sup>2,4</sup>		---	---	-7	A
VSD	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V , I <sub>S</sub> =-1A , T <sub>J</sub> =25°C	---	---	-1.2	V

Note :

- 1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width  $\leq 300\mu s$  , duty cycle  $\leq 2\%$
- 3、The power dissipation is limited by 150°C junction temperature
- 4、The data is theoretically the same as I D and I DM , in real applications , should be limited by total power dissipation.

## Typical Characteristics

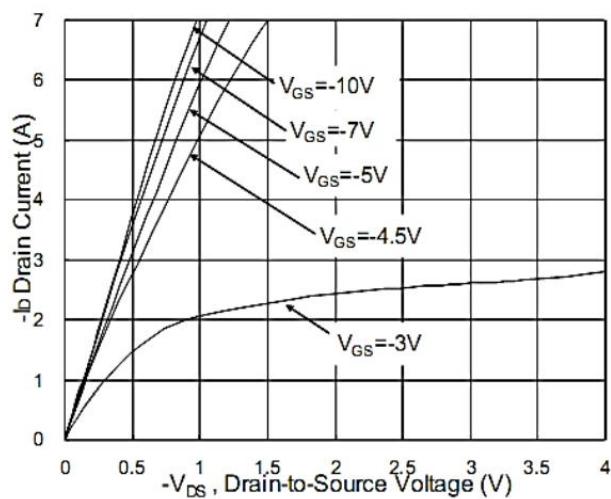


Fig.1 Typical Output Characteristics

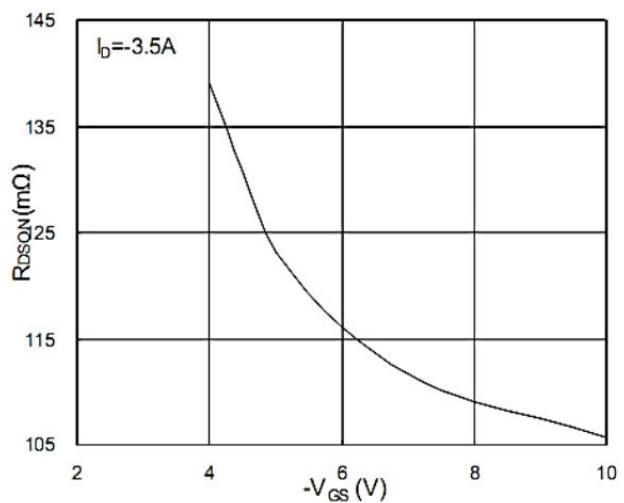


Fig.2 On-Resistance v.s Gate-Source

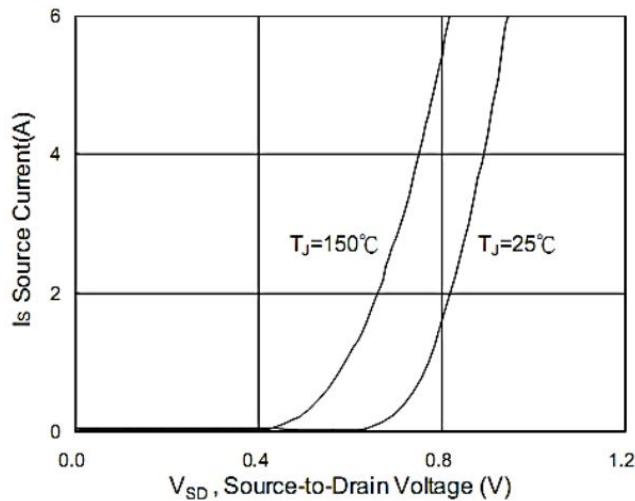


Fig.3 Forward Characteristics Of Reverse

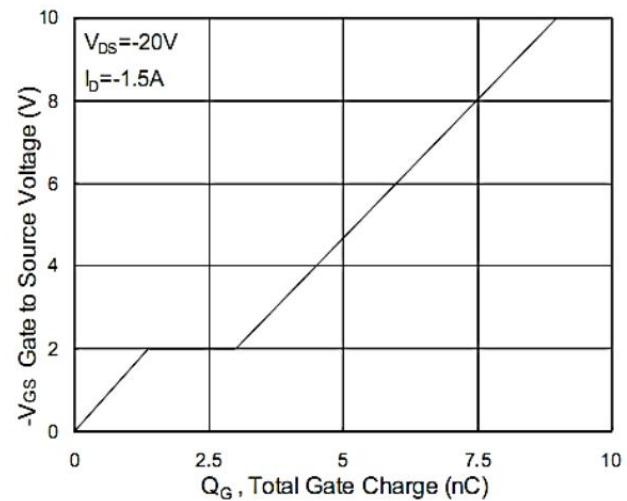


Fig.4 Gate-Charge Characteristics

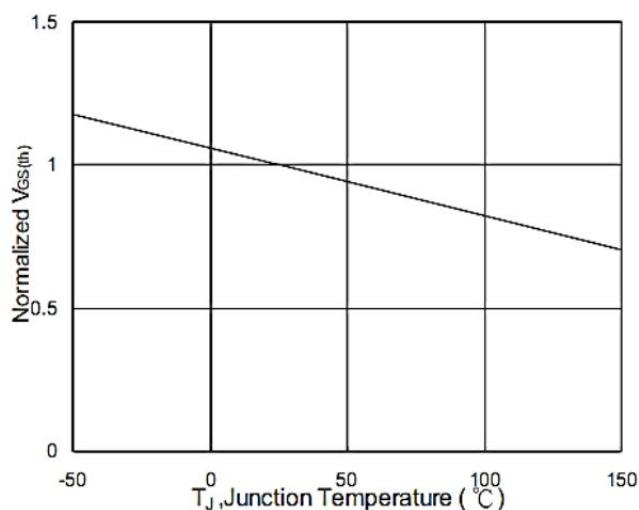


Fig.5 Normalized  $V_{GS(th)}$  v.s  $T_J$

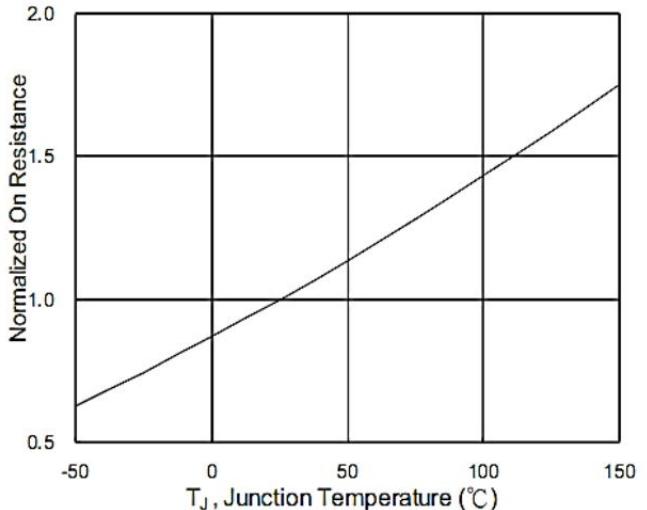


Fig.6 Normalized  $R_{DS(on)}$  v.s  $T_J$

## Typical Characteristics

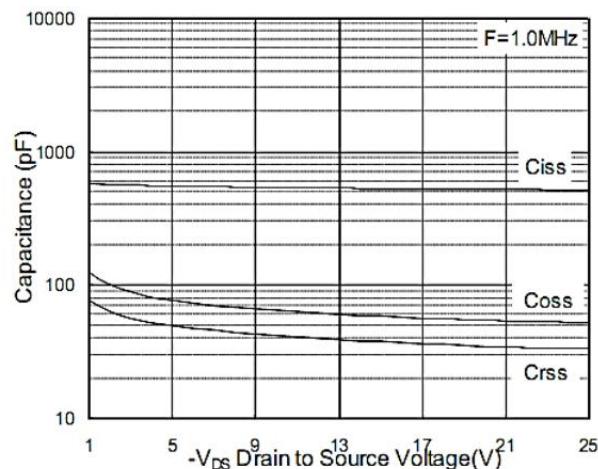


Fig.7 Capacitance

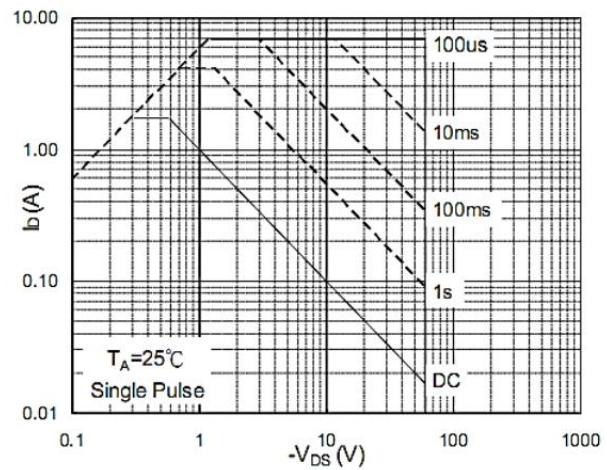


Fig.8 Safe Operating Area

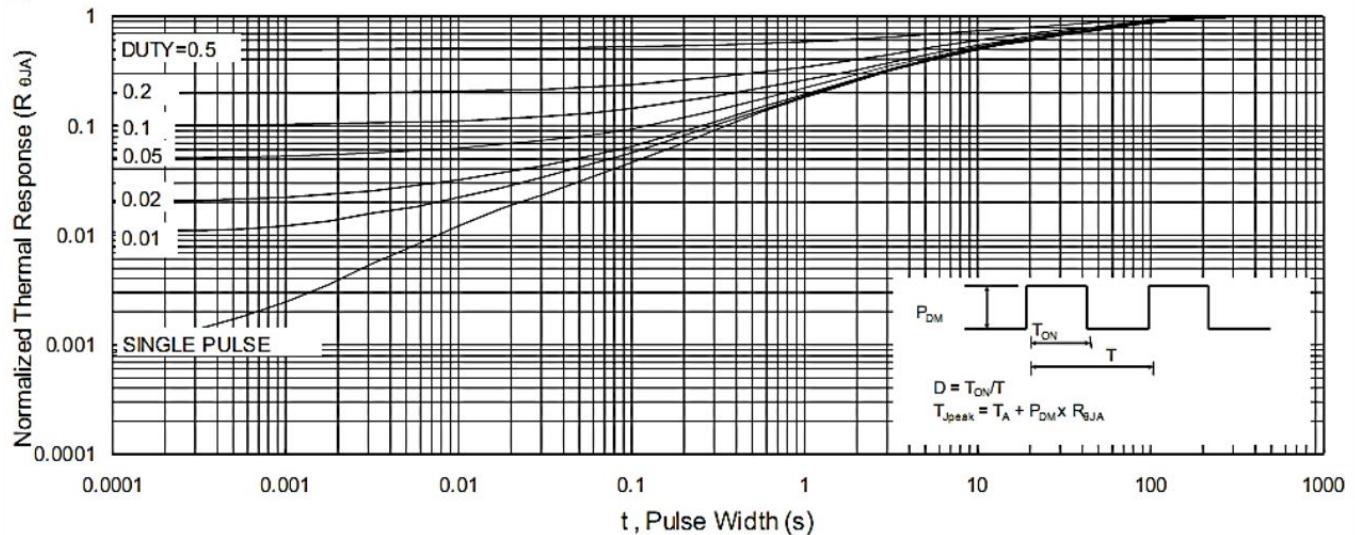


Fig.9 Normalized Maximum Transient Thermal Impedance

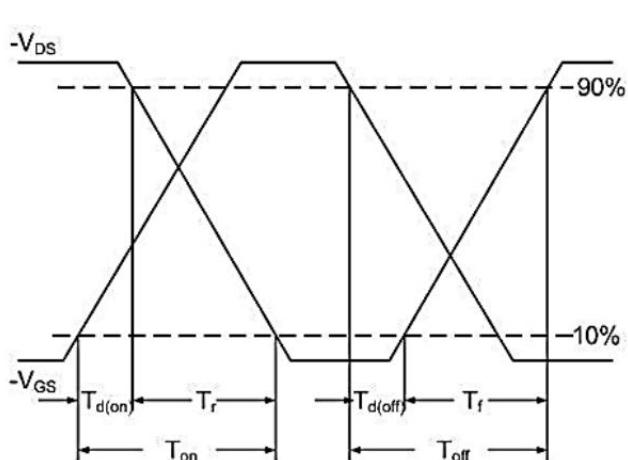


Fig.10 Switching time waveform

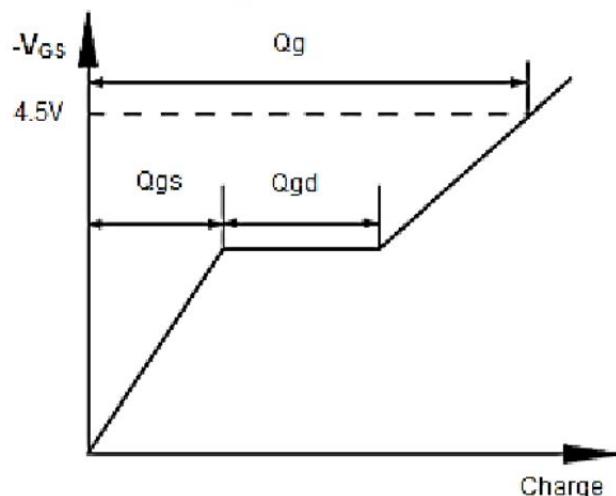
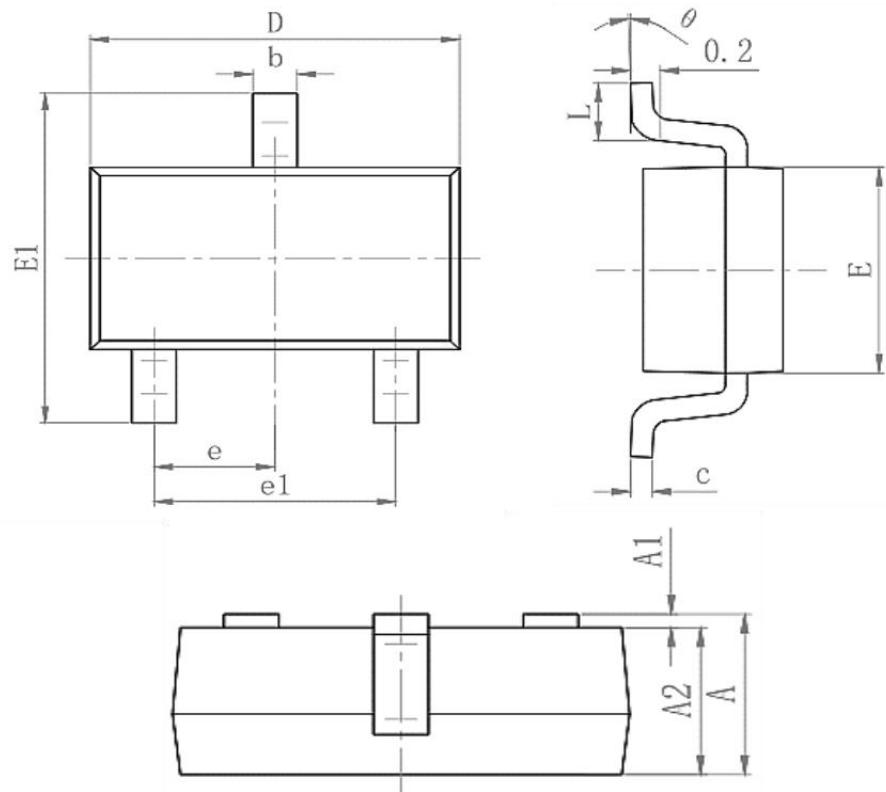


Fig.11 Gate Charge waveform

## Package Mechanical Data-SOT23-3-XC-Single



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	1.050	1.250
A1	0.000	0.100
A2	1.050	1.150
b	0.25	0.45
c	0.100	0.200
D	2.820	3.020
E	1.5	1.7
E1	2.650	2.950
e	0.950(BSC)	
e1	1.800	2.000
L	0.300	0.500
θ	0°	8°

### Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	SOT23-3L		3000